				Specifications					
No.	b. Item		Temperature Compensating Type	High Dielectric Type	- Test Method				
1	Operating Temperat Range	•	5C: -55 to +125°C	R7: –55 to +125°C R6: –30 to +85°C					
2	Rated Voltage		See the previous page	ges.	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, $V^{p,p}$ or $V^{o,p}$, whichever is larger, should be maintained within the rated voltage range.				
3	Appearar	nce	No defects or abnorr	nalities	Visual inspection				
4	Dimensio	ons	Within the specified	dimensions	Using calipers				
5	Dielectric Strength		No defects or abnorr	nalities	No failure should be ob (5C) or 250% of the rate terminations for 1 to 5 s current is less than 50m	ed voltage (R7) is seconds, provide	s applied b	etween the	
6	Insulation Resistance		More than 10,000MΩ (Whichever is smalle		The insulation resistant voltage not exceeding t max. and within 2 minut	the rated voltage			
7	Capacita	nce	Within the specified	olerance	The capacitance/Q/D.F	should be meas	sured at 25	°C at the	
			30pF min.: Q≧1000		frequency and voltage s	shown in the tabl	е.		
	Q/		30pF max.: Q≧400+20C	Char. 25V min. 16V 10V 6.3V	Char. Item	5C	R	7	
8	Dissipation Factor		Q= 1001200	R7, R6 0.025 0.035 0.035 0.05 max. max. max. max.		±0.1MHz	1±0.1	1kHz	
	(D.F.)		C: Nominal Capacitance (pF)		Voltage 0.5	5 to 5Vrms	1.0±0.	2Vrms	
9	Capacitance Temperature Characteristics	Capacitance Change Temperature Coefficent Capacitance Drift	Within the specified tolerance (Table A) Within the specified tolerance (Table A) Within ±0.2% or ±0.05pF (Whichever is larger.)	Char. Temp. Range Reference Temp. Cap. Change R7 to +125°C to +125°C to +85°C 25°C Within ±15%	3 4 125 5 125 (2) High Dielectric Cons The ranges of capacital 25°C value over the ten should be within the spectrum	ature stage. ensating Type cient is determine o 3 as a reference ly from step1 thro ecified tolerance ance change as T is calculated by div and minimum me cap. value in ste <u>Temperature</u> 25±2 ±3 (for SC/R7), - 25±2 ±3 (for SC/R7), 5 20±2 stant Type nce change com mperature ranges ecified ranges.	ed using the e. When cy- bugh 5, the for the tem Fable A. viding the d easured va p 3. e (°C) 30 ± 3 (for F 85±3 (for F pared with s shown in f	e capaci- cling the capacitance perature differences lues in the 5) 5) the above the table	
10	Adhesive Strength of Termination		GNM	removal of the terminations or other defect should occur.		he test jig (glass 6 older. Then apply 5 older. The apply 5 o	5N force in an iron or u with care so	parallel with using the o that the	

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	o. Item			Specifications						
No.			Temperature Compensating Type	High Dielectric	Туре		- Test Method			
		Appearance	No defects or abnorr	nalities			Solder the capacitor to the test jig (glass epoxy board) in the same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic motion			
		Capacitance	Within the specified t	olerance						
11	Vibration Resistance	Q/D.F.	30pF min.: Q≧1000 30pF max.: Q≧400+20C C: Nominal Capacitance (pF)	Char. 25V min. 16V R7, R6 0.025 0.035 max. max.	10V 0.035 max.	6.3V 0.05 max.	having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 55Hz. The frequency range, from 10 to 55Hz and return to 10Hz, should be traversed in approximately 1 minute. This motion should be applied for a period of 2 hours in each of 3 mutually perpendic- ular directions (total of 6 hours).			
			No cracking or marki	ng defects should occur.			Solder the capacitor on the test jig (glass epoxy board) shown			
	2 Deflection		•GNM□□4				in Fig. 2 using a eutectic solder. Then apply a force in the direction shown in Fig. 3 for 5±1 se The soldering should be done by the reflow method and shou be conducted with care so that the soldering is uniform and fr of defects such as heat shock.			
12				a b c .0±0.05 0.2±0.05 0.2±0. 0.0±0.05 0.5±0.05 0.32±0	05 0.25±	0.05	20 50 Pressurizing speed : 1.0mm/sec. Pressurize Flexure : ≤1 Capacitance meter			
			GNM212 2 GNM214 2	.0±0.05 0.6±0.05 0.5±0. .0±0.05 0.7±0.05 0.3±0. .5±0.05 0.8±0.05 0.4±0.	05 0.5± 05 0.2± 05 0.4±	0.05 0.05	Fig. 3			
13	3 Solderability of Termination		75% of the terminations are to be soldered evenly and continuously.			Immerse the capacitor in a solution of ethanol (JIS-K-8101) and rosin (JIS-K-5902) (25% rosin in weight proportion). Preheat at 80 to 120°C for 10 to 30 seconds. After preheating, immerse in eutectic solder solution for 2 ± 0.5 seconds at $230\pm5^{\circ}$ C or Sn-3.0Ag-0.5Cu solder solution for 2 ± 0.5 seconds at $245\pm5^{\circ}$ C.				
	Resistance to Soldering Heat		The measured and o specifications in the	bserved characteristics sho following table.	ould satis					
		Appearance	No marking defects							
		Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	R7, R6: Within ±7.5%			Preheat the capacitor at 120 to 150°C for 1 minute. Immerse the capacitor in a eutectic solder or Sn-3.0Ag-0.5Cu solder solution at $270\pm5°$ C for 10 ± 0.5 seconds. Let sit at room temperature for 24 ± 2 hours, then measure.			
14		Q/D.F.	30pF min.: Q≥1000 30pF max.: Q≥400+20C C: Nominal Capacitance (pF)	Char. 25V min. 16V R7, R6 0.025 0.035 max. max.	10V 0.035 max.	6.3V 0.05 max.	 Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then let sit for 24±2 hours at room temperature. Perform the initial measurement. 			
	-	I.R.	,	Ω or 500 $\Omega \cdot F$ (Whichever is	smaller)		-			
		Dielectric Strength	No failure	More than 10,000MΩ or 500Ω · F (Whichever is smaller) No failure						

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	Item		Specifications													
No.			Temperature Compensating Type	High Dielectric Type					Test Method							
15	Temperature Cycle		The measured and o specifications in the	ould sati	Fix the capacitor to the supporting jig in the same manner and											
	, ,	Appearance	No marking defects						under the sam	e conditions a	s (10). Pe	erform the five	cycles			
		Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	R7, R6: Within ±7.5%					according to the four heat treatments listed in the following table. Let sit for 24 ± 2 hours (temperature compensating type) or 48 ± 4 hours (high dielectric constant type) at room temperature, then measure.							
			30pF min.: Q≧1000						Step	1 Min.	2	3 Max.	4			
			30pF max.: Q≥400+20C	Char.	25V min.	16V	10V	6.3V	Temp. (°C)	Operating Temp. +0/–3	Room Temp.	Operating Temp. +3/-0	Room Temp.			
		Q/D.F.		R7, R6	0.025 max.	0.035 max.	0.035 max.	0.05 max.	Time (min.)	30±3	2 to 3	30±3	2 to 3			
			C:Nominal Capacitance (pF)							•		ic constant type 10°C for one he				
		I.R.	More than 10,000M	2 or 500Ω	• F (Whic	chever is	smaller)		r 24±2 hours a						
		Dielectric Strength	No failure						Perform the initial measurement.							
	Humidity State	Steady	The measured and o specifications in the	stics sh	ould sati											
		Appearance	No marking defects													
		Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	R7, R6:	Within ±	12.5%			-							
16		Q/D.F.	30pF and over: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pF and below: Q≥200+10C C: Nominal Capacitance (pF) More than 1 000MO	Char. R7, R6	0.05 max.	0.05 max	i (. n	//6.3V 0.05 nax.	hours.	95% humidity						
		I.R.	More than 1,000MΩ	or $50\Omega \cdot I$	- (Whiche	ever is s	maller)		-							
		Dielectric Strength	No failure													
	Humidity Load		The measured and observed characteristics should satisfy the specifications in the following table.													
		Appearance	No marking defects	No marking defects												
17		Capacitance Change	Within ±7.5% or ±0.75pF (Whichever is larger)	R7, R6:	Within \pm	12.5%			Apply the rated voltage at $40\pm2^{\circ}$ C and 90 to 95% humidity for							
		Q/D.F.	30pF and over: Q≥200 30pF and below: Q≥100+10C/3 C: Nominal Capacitance (pF)	Char. R7, R6	0.05	. 16V 0.05 max	0	//6.3V 1.05 nax.	500±12 hours Remove and I measure. The charge/di	et sit for 24±2		room temperat	ure, then			
		I.R.	More than 500M Ω or	25Ω · F (Whichev	er is sm	aller)									
		Dielectric Strength	No failure													

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	Item			Specifications			
No.			Temperature Compensating Type	High Dielectric Type	- Test Method		
	High Tem Load	perature	The measured and o specifications in the	bserved characteristics should satisfy the following table.			
		Appearance	No marking defects				
		Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	R7, R6: Within ±12.5%	Apply 200% of the rated voltage for 1000±12 hours at the maximum operating temperature ±3°C. Let sit for 24±2 hours at room temperature, then measure. The charge/discharge current is less than 50mA.		
18		Q/D.F.	30pF and over: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pF and below: Q≥200+10C C: Nominal Capacitance (pF)	Char. 25V min. 16V 10V/6.3V R7, R6 0.04 0.05 0.05 max. max. max. max.	 Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage for one hour at the maximum operating temperature ±3°C. Remove and let sit for 24±2 hours at room temperature. Perform initial measurement. 		
		I.R.	More than 1,000M Ω	or $50\Omega \cdot F$ (Whichever is smaller)			

Table A

	N N N N	Capacitance Change from 25°C (%)						
Char.	Nominal Values (ppm/℃) Note 1	-5	5°C	-3	℃	–10℃		
	(ppin/c) Note i	Max.	Min.	Max.	Min.	Max.	Min.	
5C	0±30	0.58	-0.24	0.40	-0.17	0.25	-0.11	

Note 1: Nominal values denote the temperature coefficient within a range of 25 to 125°C.

